

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS	L1	60759	(gate and source and drain)	USPAT	2000/08/24 09:24			0
2	BRS	L2	0	1 and (multi-insulating adj layer)	USPAT	2000/08/24 09:25			0
3	BRS	L3	10564	1 and (insulating adj layers)	USPAT	2000/08/24 09:27			0
4	BRS	L4	2	3 and HSQ	USPAT	2000/08/24 09:30			0
5	BRS	L5	200519	semiconductor	USPAT	2000/08/24 09:34			0
6	BRS	L6	24669	5 and insulating adj layers	USPAT	2000/08/24 09:36			0
7	BRS	L7	424050	6 and conductive adj film	USPAT	2000/08/24 09:39			0
8	BRS	L8	1428	6 AND CONDUCTIVE adj FILM	USPAT	2000/08/24 09:40			0
9	BRS	L9	0	8 and HSQ	USPAT	2000/08/24 09:40			0
10	BRS	L11	19	6 and 10	USPAT	2000/08/24 10:03			0
11	BRS	L12	3599	SiH	USPAT	2000/08/24 10:03			0
12	BRS	L13	1	10 and 12	USPAT	2000/08/24 10:04			0
13	BRS	L10	88	HSQ	USPAT	2000/08/24 10:09			0

	U	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	US 6090667 A	20000718	11	Method of manufacturing floating gate type transistor	438/258	438/675
2	<input type="checkbox"/>	US 5998822 A	19991207	14	Semiconductor integrated circuit and a method of manufacturing the same	257/301	257/296
3	<input type="checkbox"/>	US 5977593 A	19991102	11	Semiconductor device and method of manufacturing the same	257/356	257/315 ; 257/355 ; 257/758 ; 257/763
4	<input type="checkbox"/>	US 5877081 A	19990302	16	Method of manufacturing semiconductor device	438/624	438/636 ; 438/740 ; 438/952
5	<input type="checkbox"/>	US 5858837 A	19990112	20	Method of manufacturing semiconductor memory device	438/255	438/398
6	<input type="checkbox"/>	US 5728616 A	19980317	16	Method of making a semiconductor memory device with improved capacitor	438/240	438/253 ; 438/396
7	<input type="checkbox"/>	US 5679590 A	19971021	8	Method for manufacturing contact hole for a nonvolatile semiconductor device	438/43	438/257 ; 438/476 ; 438/586
8	<input type="checkbox"/>	US 5541444 A	19960730	30	Device and method of manufacturing the same and semiconductor device and same method of manufacturing the same	257/587	257/197 ; 257/383 ; 257/770
9	<input type="checkbox"/>	US 4579601 A	19860401	20	Method of growing a resistive epitaxial layer on a short lifetime epi-layer	438/143	438/474 ; 438/934 ; 438/953

6030706  
5,940,734  
5,728,630

HSR

6,060,384 → S.H  
5,958,798  
5,942,801  
5,888,898

5,660,849 → S.H

to wire in #ways